

# P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
-40V	15mΩ @ $V_{GS}$ = -10 $V$	-61A
	$23m\Omega$ @ $V_{GS} = -4.5V$	-49A

#### **Description and Applications**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Reverse Polarity Protection
- BLDC Motor Control
- Power Management Functions

#### **Features and Benefits**

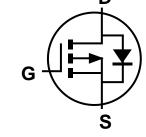
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- · Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMP4013SPSQ</u>)

#### **Mechanical Data**

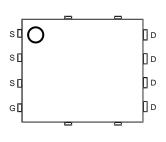
- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208<sup>(3)</sup>
- Weight: 0.097 grams (Approximate)



Top View



Internal Schematic



Top View Pin Configuration

#### **Ordering Information** (Note 4)

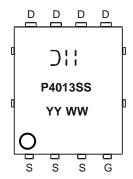
-		
Part Number	Case	Packaging
DMP4013SPS-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

**Bottom View** 

### Marking Information



);; = Manufacturer's Marking P4013SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)

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April 2019



## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	-40	V		
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current V <sub>GS</sub> = -10V (Note 7)	Steady State	$T_C = +25$ °C $T_C = +70$ °C	ΙD	-61 -49	А
Continuous Drain Current V <sub>GS</sub> = -10V (Note 6)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	Ι <sub>D</sub>	-11 -9	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-244	Α		
Maximum Body Diode Continuous Current (Note 7)	Is	-61	Α		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-244	Α
Avalanche Current (Note 8) L = 1mH	I <sub>AS</sub>	-16	Α		
Avalanche Energy (Note 8) L = 1mH	E <sub>AS</sub>	176	mJ		

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	96	°C/W
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	$P_{D}$	3.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	44	°C/W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	1.5	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	$V_{GS(TH)}$	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	9.6	15	mΩ	$V_{GS} = -10V, I_D = -10A$	
Static Dialif-Source Off-Nesistance	R <sub>DS(ON)</sub>	_	13.4	23	1112.2	$V_{GS} = -4.5V, I_D = -8A$	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	4004			.,	
Output Capacitance	Coss	_	309		pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	Crss	_	229	_		I = IIVIAZ	
Gate Resistance	$R_{g}$	_	3.5	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_g$	_	31				
Total Gate Charge (V <sub>GS</sub> = -10V)	$Q_g$	_	67	_	nC	$V_{DS} = -20V,$	
Gate-Source Charge	$Q_{gs}$	_	13.2	_	IIC	I <sub>D</sub> = -10A	
Gate-Drain Charge	$Q_{gd}$		11	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	9.9	_			
Turn-On Rise Time	t <sub>R</sub>		32	_	ns	$V_{GS} = -10V, V_{DD} = -20V,$ $R_{G} = 3\Omega, I_{D} = -10A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	46	_	115		
Turn-Off Fall Time	t <sub>F</sub>	_	53	_			
Reverse Recovery Time	t <sub>RR</sub>	_	19.5		ns	I <sub>F</sub> = -10A, di/dt = -100A/μs	
Reverse Recovery Charge	$Q_{RR}$	_	11.6	_	nC	$I_F = -10A$ , di/dt = -100A/ $\mu$ s	

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate. 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- Has and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.



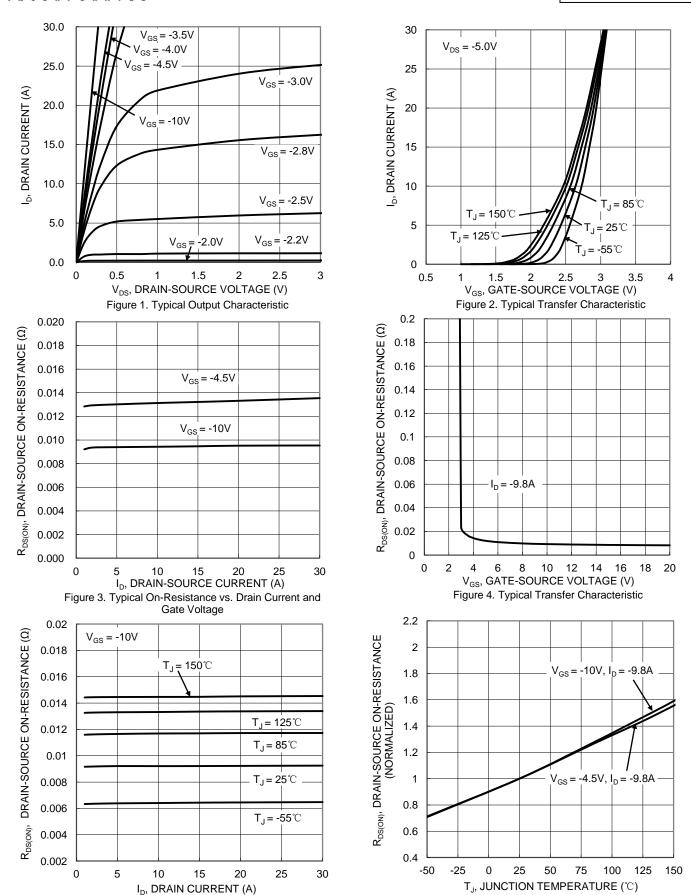
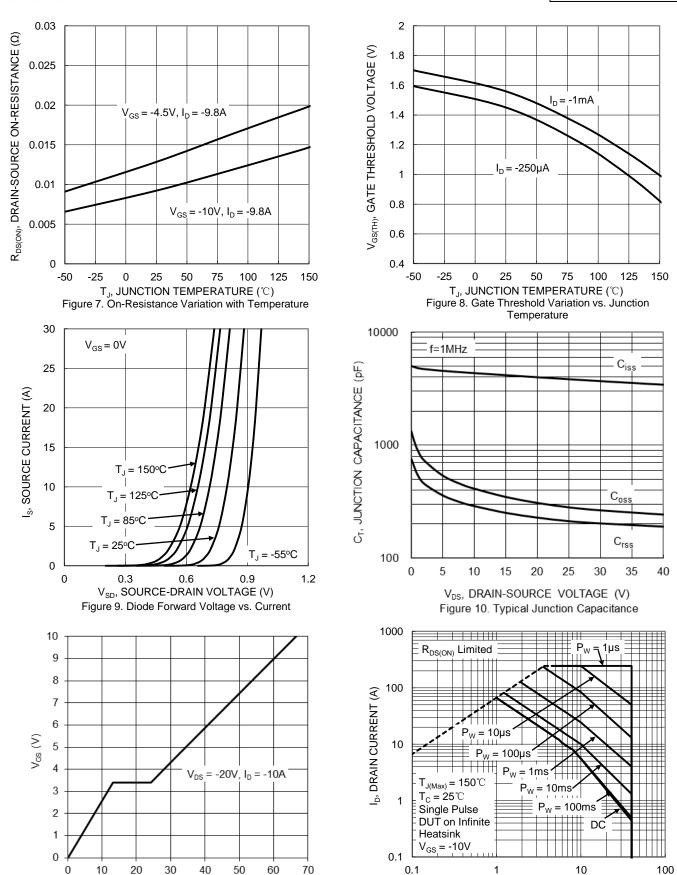


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

Figure 6. On-Resistance Variation with Temperature





Qg (nC)

Figure 11. Gate Charge

V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



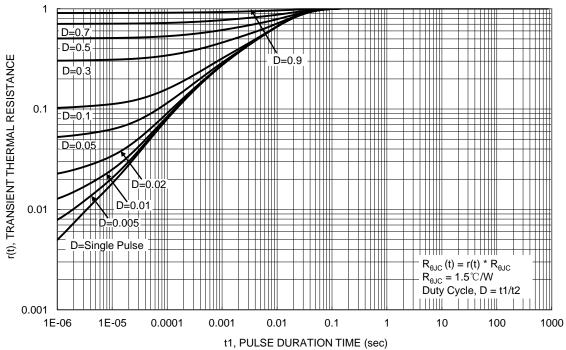


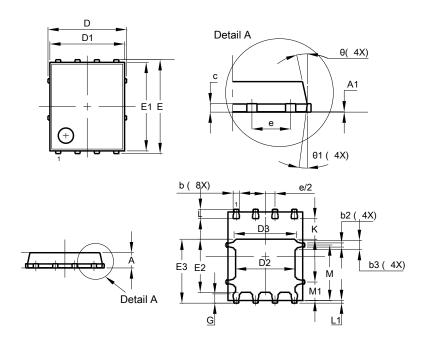
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

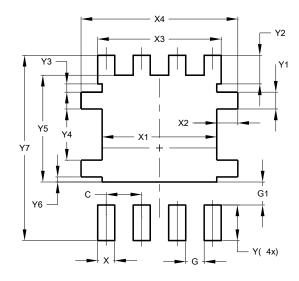


PowerDI5060-8						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	_			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D	ţ	5.15 BSC	;			
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
Е		6.15 BSC	;			
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е		1.27 BSC				
G	0.51	0.71	0.61			
K	0.51	_	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
M	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10°	12°	11°			
Θ1	6°	8°	7°			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	value (in mm)			
C	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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